

SMAF Schottky Barrier Rectifier Diode 肖特基势垒整流二极管**■Features 特点**

Low forward voltage drop 低正向压降
 High current capability 高电流能力
 Surface mount device 表面贴装器件
 Case 封装:SMAF

**■Maximum Rating 最大额定值**

(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SS36FL	Unit 单位
Peak Reverse Voltage 反向峰值电压	V _{RRM}	60	V
DC Reverse Voltage 直流反向电压	V _R	60	V
RMS Reverse Voltage 反向电压均方根值	V _{R(RMS)}	42	V
Forward Rectified Current 正向整流电流	I _F	3	A
Peak Surge Current 峰值浪涌电流	I _{FSM}	80	A
Thermal Resistance J-L 结到管脚热阻	R _{θJL}	28	°C/W
Junction Temperature 结温	T _J	125	°C
Storage Temperature 储藏温度	T _{stg}	-55 to +150	°C

■Electrical Characteristics 电特性

(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SS36FL	Unit 单位	Condition 条件
Forward Voltage 正向电压	V _F	0.55	V	I _F =3A
Reverse Current 反向电流	I _R (25°C) (125°C)	0.15 30	mA	V _R =V _{RRM}
Diode Capacitance 二极管电容	C _D	240	pF	V _R =4V, f=1MHz

■ Typical Characteristic Curve 典型特性曲线

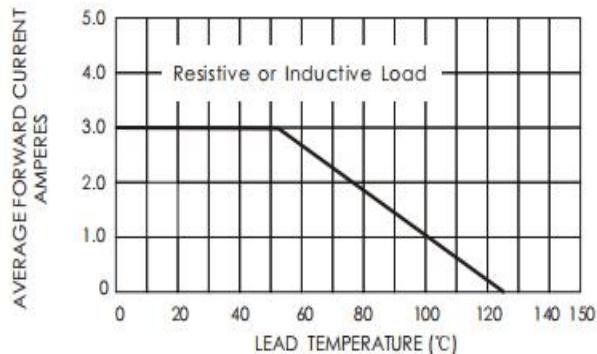


Figure 1: Forward Current Curve

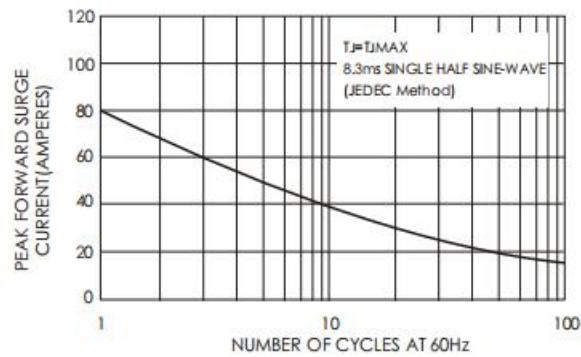


Figure 2: Forward Surge Current Curve

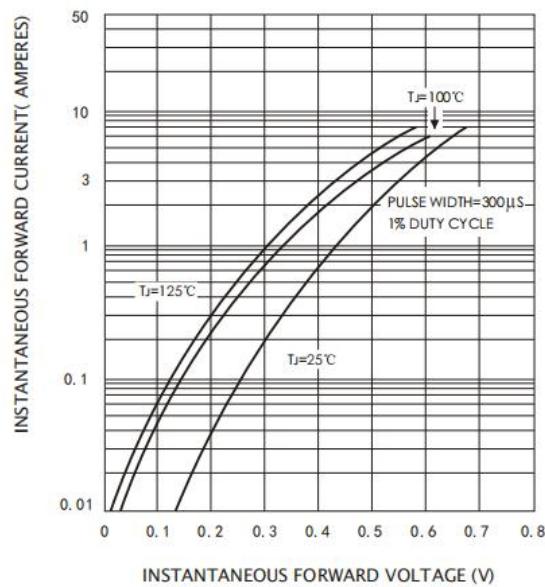


Figure 3: Forward Characteristics

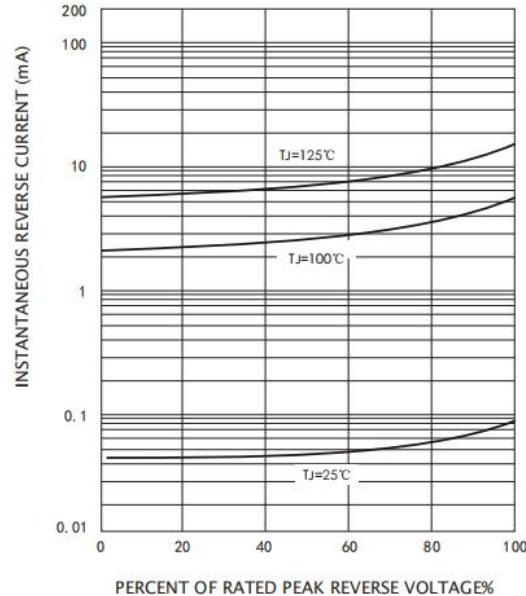


Figure 4: Reverse Characteristics

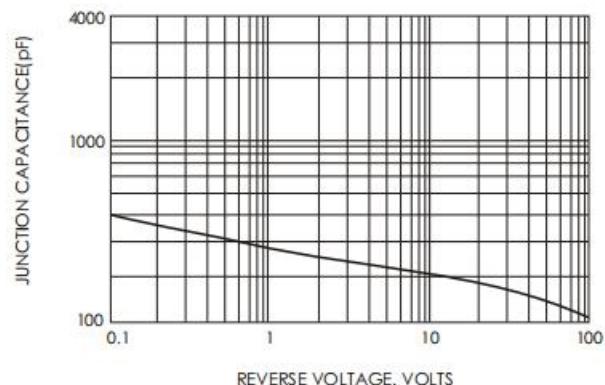


Figure 5: Capacitance Characteristics

■Dimension 外形封装尺寸

